

## **Preliminary**

## **TSM4416D**

## 30V Dual N-Channel MOSFET



SOP-8

# 5010

#### Pin Definition:

1. Source 1	8. Drain 1
2. Gate 1	7. Drain 1
3. Source 2	6. Drain 2

4. Gate 2 5. Drain 2

#### PRODUCT SUMMARY

V <sub>DS</sub> (V)	$R_{DS(on)}(m\Omega)$	I <sub>D</sub> (A)
30	19 @ V <sub>GS</sub> = 10V	8.5
	28 @ V <sub>GS</sub> = 4.5V	6

#### **Features**

- Advance Trench Process Technology
- High Density Cell Design for Ultra Low On-resistance

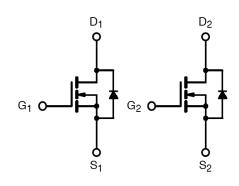
#### **Application**

- Load Switch
- PWM Application

#### **Ordering Information**

Part No. Package		Packing		
TSM4416DCS RL	SOP-8	2.5Kpcs / 13" Reel		

#### **Block Diagram**



**Dual N-Channel MOSFET** 

#### **Absolute Maximum Rating** (Ta = 25°C unless otherwise noted)

Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		$V_{DS}$	30	V	
Gate-Source Voltage		$V_{GS}$	20	V	
Continuous Drain Current		I <sub>D</sub>	8.5	А	
Pulsed Drain Current		I <sub>DM</sub>	40	А	
Continuous Source Current (Diode Conduction) <sup>a,b</sup>		I <sub>S</sub>	2.6	А	
Maximum Power Dissipation	Ta = 25°C	Б	2.5	W	
	Ta = 75°C	- P <sub>D</sub>	1.6		
Operating Junction Temperature		TJ	+150	°C	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	- 55 to +150	°C	

#### **Thermal Performance**

Parameter	Symbol	Limit	Unit	
Junction to Case Thermal Resistance	RΘ <sub>JF</sub>	25	°C/W	
Junction to Ambient Thermal Resistance (PCB mounted)	RO <sub>JA</sub>	50	°C/W	

#### Notes:

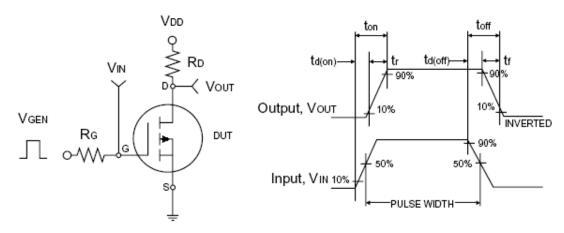
- a. Pulse width limited by the Maximum junction temperature
- b. Surface Mounted on FR4 Board,  $t \le 10$  sec.



#### **Electrical Specifications** (Ta = 25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static	Static					
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250uA$	BV <sub>DSS</sub>	30	I		V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	$V_{GS(TH)}$	1	1.8	3	V
Gate Body Leakage	$V_{GS} = \pm 20V, V_{DS} = 0V$	I <sub>GSS</sub>		I	±100	nA
Zero Gate Voltage Drain Current	$V_{DS} = 24V, V_{GS} = 0V$	I <sub>DSS</sub>		I	-1.0	μA
On-State Drain Current <sup>a</sup>	V <sub>DS</sub> ≥ 5V, V <sub>GS</sub> = 10V	I <sub>D(ON)</sub>	40	I		Α
Drain-Source On-State Resistance	$V_{GS} = 10V, I_D = 8.5A$	В		15.5	19	m0
Diain-Source On-State Resistance	Source On-State Resistance $V_{GS} = 4.5V$ , $I_D = 6A$		23	28	mΩ	
Forward Transconductance <sup>a</sup>	$V_{DS} = 5V, I_{D} = 8.5A$	g <sub>fs</sub>		23		S
Diode Forward Voltage	$I_{S} = 1A, V_{GS} = 0V$	$V_{SD}$		0.71	1.0	V
Dynamic <sup>b</sup>		_				
Total Gate Charge	\/ - 15\/   - 0.5\	$Q_g$		19	24	
Gate-Source Charge	$V_{DS} = 15V, I_D = 8.5A,$ $V_{GS} = 5V$	$Q_gs$		9.36	12	nC
Gate-Drain Charge	V <sub>GS</sub> – 5V	$Q_{gd}$		4.2		
Input Capacitance	$V_{DS} = 15V, V_{GS} = 0V,$	C <sub>iss</sub>		1040		
Output Capacitance	$v_{DS} = 15v, v_{GS} = 0v,$ f = 1.0MHz	C <sub>oss</sub>		180		pF
Reverse Transfer Capacitance	1 - 1.0IVINZ	$C_{rss}$		110		
Switching <sup>c</sup>						
Turn-On Delay Time	V - 15V D - 100	t <sub>d(on)</sub>		5.2		
Turn-On Rise Time	$V_{DD} = 15V, R_L = 1.8\Omega,$	t <sub>r</sub>		4.4		nS
Turn-Off Delay Time	$I_D = 1A, V_{GEN} = 10V,$ $R_G = 3\Omega$	$t_{d(off)}$		17.3		113
Turn-Off Fall Time	11G - 312	t <sub>f</sub>		3.3		

- a. pulse test: PW ≤300µS, duty cycle ≤2% b. For DESIGN AID ONLY, not subject to production testing.
- b. Switching time is essentially independent of operating temperature.



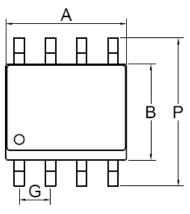
**Switching Test Circuit** 

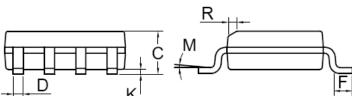
Switchin Waveforms





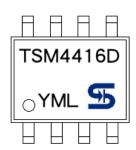
## **SOP-8 Mechanical Drawing**





SOP-8 DIMENSION					
DIM	MILLIMETERS		INCHES		
DIIVI	MIN	MAX	MIN	MAX.	
Α	4.80	5.00	0.189	0.196	
В	3.80	4.00	0.150	0.157	
С	1.35	1.75	0.054	0.068	
D	0.35	0.49	0.014	0.019	
F	0.40	1.25	0.016	0.049	
G	1.27	BSC	0.05	BSC	
K	0.10	0.25	0.004	0.009	
М	0°	7°	0°	7°	
Р	5.80	6.20	0.229	0.244	
R	0.25	0.50	0.010	0.019	

## **Marking Diagram**



Y = Year Code

**M** = Month Code

(A=Jan, B=Feb, C=Mar, D=Apl, E=May, F=Jun, G=Jul, H=Aug, I=Sep, J=Oct, K=Nov, L=Dec)

**L** = Lot Code



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4/4 Version: Preliminary